Dr.T.S.Arun Samuel.

List of publication in past 5years

TITLE	YEAR
Investigation of Cylindrical Channel Gate All Around InGaAs/InP Heterojunction Heterodielectric Tunnel FETs P Vimala, TSA Samuel Silicon, 1-9	2020
Modeling and simulation of a dual-material asymmetric heterodielectric- gate TFET IV Anand, TSA Samuel, P Vimala Journal of Computational Electronics, 1-13	2020
Performance Investigation of Gate Engineered tri-Gate SOI TFETs with Different High-K Dielectric Materials for Low Power Applications P Vimala, TSA Samuel, MK Pandian Silicon 12 (8), 1819-1829	2020
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